

# NPN SILICON RF TRANSISTOR

**DESCRIPTION:**

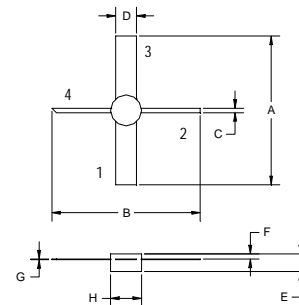
The **MRF750** is Designed for UHF Large Signal Amplifier Application from 407 to 512 MHz, and 5.0 to 10 V.

**FEATURES INCLUDE:**

- High Power Gain
- Infinite VSWR

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	200 mA
<b>V<sub>CE</sub></b>	13 V
<b>P<sub>DISS</sub></b>	2.5 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +150 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	28.5 °C/W

**PACKAGE STYLE .205" 4L PILL**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.00 / 25.400
B	.976 / 24.800	1.00 / 25.400
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.106 / 2.700	.139 / 3.400
F	.039 / 1.000	.047 / 1.200
G	.004 / 0.100	.006 / 0.150
H	.200 / 5.100	.208 / 5.300

1 & 3 = EMITTER    2 = BASE  
4 = COLLECTOR

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 10 mA	13			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA	25			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	4.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 9.0 V			500	<b>μA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 50 mA	20	70		<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 7.5 V    f = 1.0 MHz		3.5	5.0	<b>pF</b>
<b>G<sub>PE</sub></b> <b>η</b>	V <sub>CC</sub> = 7.5 V    P <sub>out</sub> = 500 mW    fo = 470 MHz	10 55	11		<b>dB</b> <b>%</b>